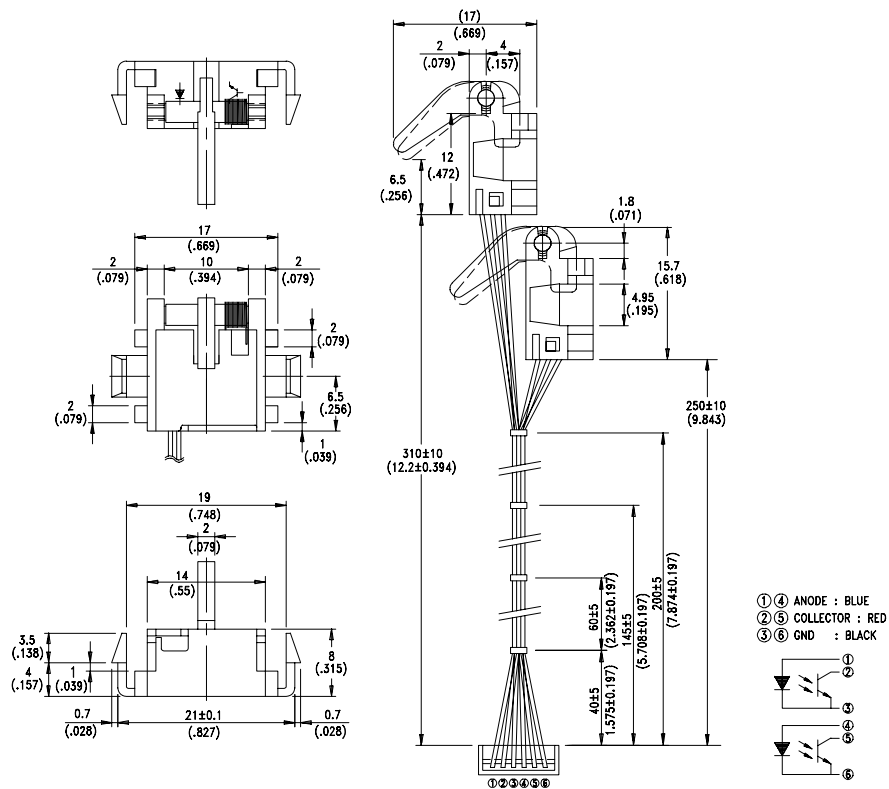


FEATURES

- * SNAP MOUNTING.
- * MECHANICAL SWITCH REPLACEMENT.
- * THREE WIRES FOR ELECTRICAL CONNECTION.
- * CUSTOMIZED LEVER ARM CAN BE DESIGNED FOR SPECIFIC APPLICATION.

PACKAGE DIMENSIONS



NOTES:

1. All dimensions are in millimeters (inches).
2. Tolerance is $\pm 0.25\text{mm}(.010\text{'})$ unless otherwise noted.

ABSOLUTE MAXIMUM RATINGS AT T_A=25

PARAMETER	MAXIMUM RATING	UNIT
IR Diode Continuous Forward Current	50	mA
IR Diode Reverse Voltage	5	V
Transistor Collector Current	20	mA
Transistor Power Dissipation	75	mW
IR Diode Peak Forward Current (Pulse Wide = 10 μ S, 300 pps)	1	A
Diode Power Dissipation	60	mW
Phototransistor Collector-Emitter Voltage	30	V
Phototransistor Emitter-Collector Voltage	5	V
Operating Temperature Range	-25 to + 85	
Storage Temperature Range	-55 to + 100	
Lead Soldering Temperature [1.6mm (.063") Form Case]	260 for 5 Seconds	

ELECTRICAL OPTICAL CHARACTERISTICS AT T_A=25

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
INPUT LED						
Forward Voltage	V _F		1.2	1.6	V	I _F = 20mA
Reverse Current	I _R			100	μ A	V _R =5V
OUTPUT PHOTOTRANSISTOR						
Collector-Emitter Breakdown Voltage	V(BR) _{CEO}	30			V	I _C =1mA
Emitter-Collector Breakdown Voltage	V(BR) _{ECO}	5			V	I _E =100 μ A
Collector-Emitter Dark Current	I _{CEO}			100	nA	V _{CE} =10V
COUPLER						
Collector-Emitter Saturation Voltage	V _{CE(SAT)}			0.4	V	I _C =0.2mA I _F =20mA
On State Collector Current	I _{c(ON)}	0.5	2		mA	V _{CE} =5V I _F =20mA

TYPICAL ELECTRICAL / OPTICAL CHARACTERISTICS CURVES

(25 Ambient Temperature Unless Otherwise Noted)

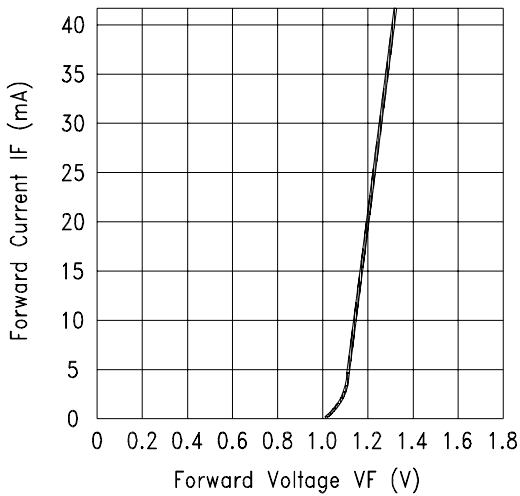


Fig.1 FORWARD CURRENT VS. FORWARD VOLTAGE

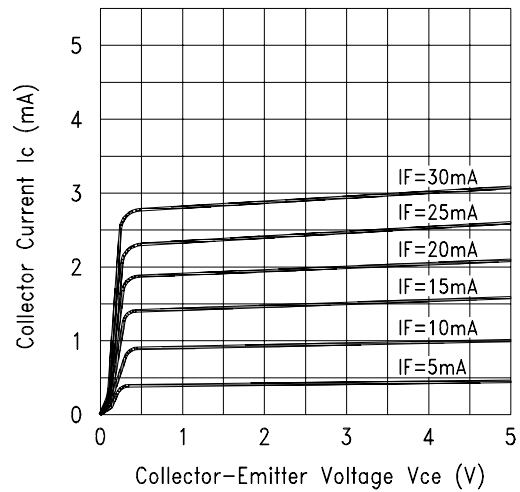


Fig.2 COLLECTOR CURRENT VS. COLLECTOR VOLTAGE

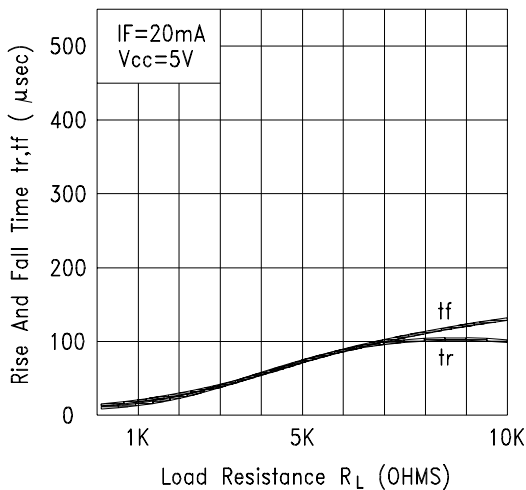


Fig.3 RISE AND FALL TIME VS. LOAD RESISTANCE

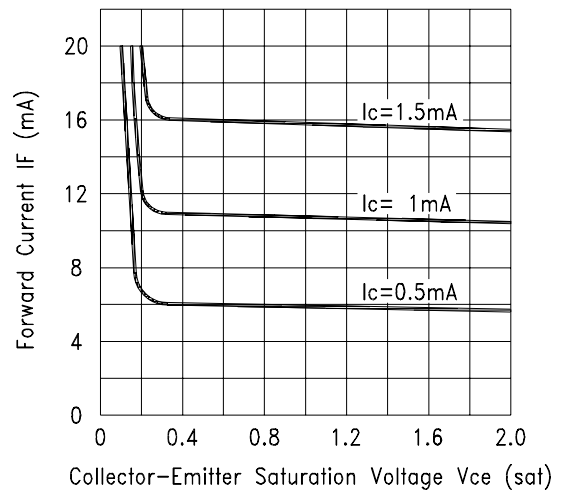


Fig.4 FORWARD CURRENT VS. Collector-Emitter Saturation Voltage